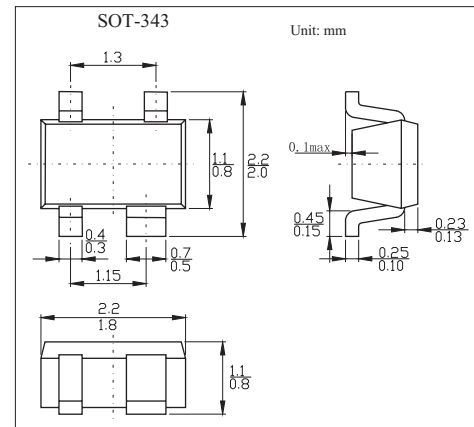


■ Features

- Low barrier diode for detectors up to GHz frequencies.



■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	40	V
Forward current	$I_F$	20	mA
Total power dissipation, $T_s = 103^\circ\text{C}$	$P_{tot}$	100	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55 to + 150	$^\circ\text{C}$
Junction - ambient	$R_{th JA}$	$\leq 630$	K/W
Junction - soldering point	$R_{th JS}$	$\leq 470$	K/W

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse current	$I_R$	$V_R = 40\text{ V}$			10	$\mu\text{ A}$
Forward voltage	$V_F$	$I_F = 2\text{ mA}$		0.58	1	V
Diode capacitance	$C_T$	$f = 1\text{ MHz}; V_R = 0$		0.35	0.6	pF
Case capacitance	$C_C$	$f = 1\text{ MHz}$		0.1		pF
Differential resistance	$R_O$	$V_R = 0, f = 10\text{ KHz}$		225		K $\Omega$
Series inductance chip to ground	$L_S$			2		nH

■ Marking

Marking	62s
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